

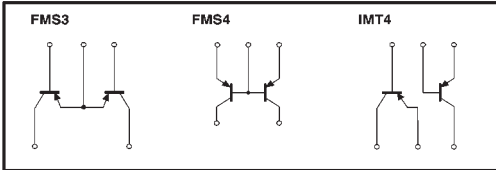
# General purpose (dual transistors)

## FMS3 / FMS4 / IMT4

### ●Features

- Two 2SA1514K chips in an SMT package.
- High breakdown voltage.

### ●Circuit diagrams



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	-120	V
Collector-emitter voltage	V <sub>CE0</sub>	-120	V
Emitter-base voltage	V <sub>EB0</sub>	-5	V
Collector current	I <sub>c</sub>	-50	mA
Power dissipation	P <sub>c</sub>	300 (TOTAL)	mW *
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

\* 200mW per element must not be exceeded.

### ●Package, marking, and packaging specifications

Part No.	FMS3	FMS4	IMT4
Package	SMT5	SMT5	SMT6
Marking	S3	S4	T4
Code	T148	T148	T108
Basic ordering unit (pieces)	3000	3000	3000

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	-120	—	—	V	I <sub>c</sub> =-50 μA
Collector-emitter breakdown voltage	BV <sub>CE0</sub>	-120	—	—	V	I <sub>c</sub> =-1mA
Emitter-base breakdown voltage	BV <sub>EB0</sub>	-5	—	—	V	I <sub>e</sub> =-50 μA
Collector cutoff current	I <sub>CB0</sub>	—	—	-0.5	μA	V <sub>CB</sub> =-100V
Emitter cutoff current	I <sub>EB0</sub>	—	—	-0.5	μA	V <sub>EB</sub> =-4V
DC current transfer ratio	h <sub>FE</sub>	180	—	820	—	V <sub>CE</sub> =-6V, I <sub>c</sub> =2mA
Transition frequency	f <sub>t</sub>	—	140	—	MHz	V <sub>CE</sub> =-12V, I <sub>e</sub> =2mA, f=100MHz*
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	—	—	-0.5	V	I <sub>c</sub> /I <sub>B</sub> =-10mA/-1mA

\*Transition frequency of the device.

(94S-389-A41)

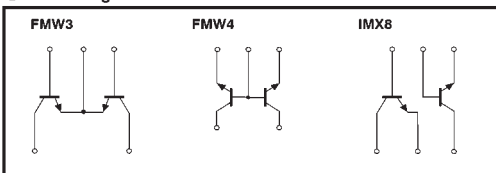
# General purpose (dual transistors)

## FMW3 / FMW4 / IMX8

### ●Features

- Two 2SC3906K chips in an SMT package.
- High breakdown voltage.

### ●Circuit diagrams



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	120	V
Collector-emitter voltage	V <sub>CE0</sub>	120	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Collector current	I <sub>c</sub>	50	mA
Power dissipation	P <sub>c</sub>	300 (TOTAL)	mW *
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

\* 200mW per element must not be exceeded.

### ●Package, marking, and packaging specifications

Part No.	FMW3	FMW4	IMX8
Package	SMT5	SMT5	SMT6
Marking	S3	S4	T4
Code	T148	T148	T108
Basic ordering unit (pieces)	3000	3000	3000

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	120	—	—	V	I <sub>c</sub> =50 μA
Collector-emitter breakdown voltage	BV <sub>CE0</sub>	120	—	—	V	I <sub>c</sub> =1mA
Emitter-base breakdown voltage	BV <sub>EB0</sub>	5	—	—	V	I <sub>e</sub> =50 μA
Collector cutoff current	I <sub>CB0</sub>	—	—	0.5	μA	V <sub>CB</sub> =100V
Emitter cutoff current	I <sub>EB0</sub>	—	—	0.5	μA	V <sub>EB</sub> =4V
DC current transfer ratio	h <sub>FE</sub>	180	—	820	—	V <sub>CE</sub> =6V, I <sub>c</sub> =2mA
Transition frequency	f <sub>t</sub>	—	140	—	MHz	V <sub>CE</sub> =-12V, I <sub>e</sub> =2mA, f=100MHz*
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	—	—	0.5	V	I <sub>c</sub> /I <sub>B</sub> =10mA/1mA

\*Transition frequency of the device

(94S-398-C41)